捷多邦,专业PCB打样工厂,24小时加急出**译4ACT11032** QUADRUPLE 2-INPUT POSITIVE-OR GATES

SCAS008C - JULY 1987 - REVISED APRIL 1996

- Inputs Are TTL-Voltage Compatible
- Center-Pin V_{CC} and GND Configurations to Minimize High-Speed Switching Noise
- **EPIC**[™] (Enhanced-Performance Implanted CMOS) 1-µm Process
- 500-mA Typical Latch-Up Immunity at 125°C
- **Package Options Include Plastic** Small-Outline Packages (D), Plastic Shrink Small-Outline Packages (DB), Plastic Thin Shrink Small-Outline Packages (PW), and Standard Plastic 300-mil DIPs (N)

D, DB, N, OR PW PACKAGE (TOP VIEW) 1A [15 7 2A 1Y [2Y [] 3 14 2B 13 VCC GND [GND [12 VCC 3Y [11 🛮 3A 4Y ∏ 10 **∏** 3B 4B **∏** 8 9**∏** 4A

description

This device contains four independent 2-input OR gates. It performs the Boolean function Y = A + B or WWW.DZSC.CC $Y = \overline{\overline{A} \bullet \overline{B}}$ in positive logic.

The 74ACT11032 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE (each gate)

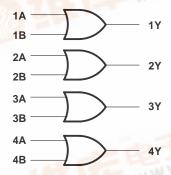
INP	UTS	OUTPUT
Α	В	Y
Н	Χ	Н
Х	Н	Н
L	L	L

logic symbol†



[†]This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†						
Supply voltage range, V _{CC} –0.5 V to 6V						
Input voltage range, V_I (see Note 1)						
Output voltage range, V_O (see Note 1)						
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ± 20 mA						
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$)						
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ± 50 mA						
Continuous current through V _{CC} or GND ±100 mA						
Maximum power dissipation at T _A = 55°C (in still air) (see Note 2): D package						
DB package 0.55 W						

Storage temperature range, T_{stq} – 65°C to 150°C

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

N package 1.1 W PW package 0.5 W

recommended operating conditions

		MIN	MAX	UNIT
Vсс	Supply voltage	4.5	5.5	V
VIH	High-level input voltage	2		V
V_{IL}	Low-level input voltage		0.8	V
VI	Input voltage	0	VCC	V
VO	Output voltage	0	VCC	V
IOH	High-level output current		-24	mA
lOL	Low-level output current		24	mA
Δt/Δν	Input transition rise or fall rate	0	10	ns/V
T _A	Operating free-air temperature	-40	85	°C



[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

^{2.} The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils, except for the N package, which has a trace length of zero.

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	vcc	T _A = 25°C			MINI	MAV	UNIT
PARAMETER			MIN	TYP	MAX	MIN	MAX	UNII
V _{ОН}	I _{OH} = -50 μA	4.5 V	4.4			4.4		V
		5.5 V	5.4			5.4		
	I _{OH} = -24 mA	4.5 V	3.94			3.8		
		5.5 V	4.94			4.8		
	$I_{OH} = -75 \text{ mA}^{\dagger}$	5.5 V				3.85		
	I _{OL} = 50 μA	4.5 V			0.1		0.1	٧
		5.5 V			0.1		0.1	
VOL	I _{OL} = 24 mA	4.5 V			0.36		0.44	
		5.5 V			0.36		0.44	
	$I_{OL} = 75 \text{ mA}^{\dagger}$	5.5 V					1.65	
lį	$V_I = V_{CC}$ or GND	5.5 V			±0.1		±1	μΑ
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			4		40	μΑ
Δl _{CC} ‡	One input at 3.4 V, Other inputs at GND or V _{CC}	5.5 V			0.9		1	mA
Ci	$V_I = V_{CC}$ or GND	5 V		3.5				pF

[†] Not more than one output should be tested at a time, and the duration of the test should not exceed 10 ms.

switching characteristics over recommended ranges of supply voltage and free-air temperature (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	T _A = 25°C			MIN	MAX	UNIT
			MIN	TYP	MAX	IVIIIV	WAX	UNIT
^t PLH	A or B	V	1.5	6.2	8.1	1.5	9	no
[†] PHL		ſ	1.5	4.9	7.4	1.5	8	ns

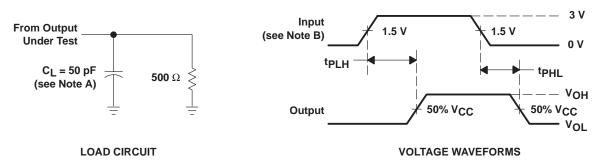
operating characteristics, $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$

	PARAMETER	TEST CON	TYP	UNIT	
C _{pd}	Power dissipation capacitance per gate	$C_L = 50 pF$,	f = 1 MHz	29	pF



[‡] This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or VCC.

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_O = 50 \Omega$, $t_f = 3 \text{ ns}$, $t_f = 3 \text{ ns}$.
- C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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